Characterizing the Interface Scaling of High $\chi_e$ Block Copolymers near the Order–Disorder Transition

Daniel F. Sunday,*† Michael J. Maher,‡ Adam F. Hannon,† Christopher D. Liman,† Summer Tein,§ Gregory Blachut,∥ Yusuke Asano,† Christopher J. Ellison,§ C. Grant Willson,∥ R. Joseph Kline†

†Materials Science and Engineering Division, National Institute of Standards and Technology, Gaithersburg, Maryland 20899-1070, United States
‡Department of Chemistry and §McKetta Department of Chemical Engineering, University of Texas at Austin, Austin, Texas 78712, United States
∥Department of Chemical Engineering and Materials Science, University of Minnesota, Minneapolis, Minnesota 55455, United States

ABSTRACT: Advancements in the directed self-assembly of block copolymers (BCPs) have prompted the development of new materials with larger effective interaction parameters ($\chi_e$). This enables BCP systems with phase separation at increasingly small degrees of polymerization ($N$). Very often these systems reside near the order–disorder transition and fit between the weak and strong segregation limits where the behavior of BCP systems is not as thoroughly understood. Utilizing resonant soft X-ray reflectivity (RSoXR) enables both the BCP pitch ($L_0$) and interface width ($w_M$) to be determined simultaneously, through a direct characterization of the composition profile of BCP lamellae oriented parallel to a substrate. A series of high $\chi_e$ BCPs with $\chi_e$ ranging from $\approx 0.04$ to $0.25$ and $\chi_eN$ from 19 to 70 have been investigated. The $L_0/w_M$ ratio serves as an important metric for the feasibility of a material for nanopatterning applications; the results of the RSoXR measurement are used to establish a relationship between $\chi_e$ and $L_0/w_M$. The results of this analysis are correlated with experimentally established limits for the functionality of BCPs in nanopatterning applications. These results also provide guidance for the magnitude of $\chi_e$ needed to achieve small interface width for samples with sub-10 nm $L_0$.

INTRODUCTION

Block copolymers (BCPs) offer intriguing possibilities as templates for patterning membranes, metal oxides, and other lithographically useful structures. The most commonly studied BCP systems reside near the order–disorder transition and fit between the weak and strong segregation limits where the behavior of BCP systems is not as thoroughly understood. Utilizing resonant soft X-ray reflectivity (RSoXR) enables both the BCP pitch ($L_0$) and interface width ($w_M$) to be determined simultaneously, through a direct characterization of the composition profile of BCP lamellae oriented parallel to a substrate. A series of high $\chi_e$ BCPs with $\chi_e$ ranging from $\approx 0.04$ to $0.25$ and $\chi_eN$ from 19 to 70 have been investigated. The $L_0/w_M$ ratio serves as an important metric for the feasibility of a material for nanopatterning applications; the results of the RSoXR measurement are used to establish a relationship between $\chi_e$ and $L_0/w_M$. The results of this analysis are correlated with experimentally established limits for the functionality of BCPs in nanopatterning applications. These results also provide guidance for the magnitude of $\chi_e$ needed to achieve small interface width for samples with sub-10 nm $L_0$.

Received: September 13, 2017
Revised: November 13, 2017
Published: December 15, 2017

DOI: 10.1021/acs.macromol.7b01982
of BCPs under these conditions. For example, Fredrickson–Helfand theory introduces a correction to the ODT prediction which results in an increase in $(\chi N)_{\text{ODT}}$ for shorter polymer chains to account for fluctuation effects. 30 The renormalized one-loop theory (ROL) was developed in an attempt to model BCP behavior over a wide parameter space. Unlike the earlier theories which depend on $N$, predictions made by this theory depend on the invariant degree of polymerization, $\tilde{N} (\tilde{N} = NB^2/\nu e^2)$. 31,32 ROL predicts that composition fluctuations result in an upward shift of $(\chi N)_{\text{ODT}}$ according to eq 2, which is an empirical relationship derived by analyzing the results of multiple simulation models. The $L_0$ scaling of lamellar BCPs depends on whether the system is in the weak-segregation-limit regime (WSL, $\chi N$ near the ODT), where $L_0 \approx N^{1/2}$ or the strong-segregation-limit regime (SSL, $\chi N \gg 10.5$) where $L_0 \approx \chi^{-1/6}N^{2/3}$. A crossover regime where $L_0 \approx N^{4/5}$ has also been observed while transitioning between the WSL and the SSL. 33–36

$$N = \frac{M_b}{\rho_vN_\chi}$$  \hspace{1cm} (1)

$$(\chi N)_{\text{ODT}} = 10.495 + 41\tilde{N}^{-1/3} + 123\tilde{N}^{-0.56}$$  \hspace{1cm} (2)

In addition to the pitch scaling, there has also been significant investigation into the interface between the two components of a BCP. 37–40 In the WSL the BCP profile is expected to take a sinusoidal shape and show incomplete segregation of the two blocks. In the SSL the two blocks are expected to show a square wave profile with an interface width being inversely proportional to $\chi^{-1/2}$. The interface width between BCP components is typically measured using specular X-ray or neutron reflectivity, which measures the scattering length density (SLD) profile as a function of depth in the film. 40–44 The SLD profile can then be transformed into a composition profile, allowing direct investigation of the composition of a BCP with lamella oriented parallel to the substrate. Historically, neutron reflectivity was the primary tool for these measurements, as the contrast between organic materials for hard X-rays was typically insufficient for accurate structural determination. The drawback to this technique is that it generally requires one of the blocks to be deuterated to enhance the contrast and reduce the incoherent background. This can be synthetically challenging for some materials and can influence the thermodynamics between the blocks. 45 Resonant soft X-ray reflectivity (RSoXR) has emerged recently as a method for enhancing contrast of the native materials based on the type and density of chemical functional groups in the blocks. 46–50 In the soft X-ray region (100–3000 eV) there are absorption edges for the atoms which are the primary constituents of most polymers, carbon ($\approx$285 eV), nitrogen ($\approx$400 eV), and oxygen ($\approx$540 eV). In the vicinity of the absorption edge, the complex refractive index ($n = 1 - (\lambda^2/2\pi)(\rho_\text{S} - \rho_\text{I})$, where $\lambda$ is the wavelength, $\rho_\text{S}$ is the real, or dispersive, component, and $\rho_\text{I}$ is the imaginary, or absorptive, component in terms of SLD) will vary sharply. The magnitude of this change depends on the proximity of the beam energy to the absorption edge location (which will shift depending on the exact chemistry) and density of the functional groups. The measured interface width from this composition profile ($w_M$) is determined by modeling the interface as an error function, and the width of the error function ($\sigma$) is then converted to $w_M$ using eq 3.

$$w_M = \sigma\sqrt{2\pi}$$  \hspace{1cm} (3)

Accurate characterization of the interfacial width is important for lithographic materials as it is potentially a limiting factor in the performance of a BCP as an etch mask. 51 Polystyrene-b-poly(methyl methacrylate) (PS-b-PMMA) is the most commonly explored material for lithographic applications, but it suffers from a number of limitations. Recent results have shown that while the material will form regular patterns down to $L_0 \approx 18$ nm, the pattern will not effectively transfer to the underlying substrate at that length scale. 11 Additionally, PS-b-PMMA generally requires enhanced etch selectivity through an additional process such as sequential infiltration synthesis. 12–54 The combination of these two challenges has prompted the development of new BCPs capable of achieving smaller pitches and/or with inherently larger etch contrast. Larger $\chi$ are generally achieved by increasing the difference in polarity between the two blocks. For example, the addition of a tert-butyl group to the PS block of PS-b-PMMA enables $L_0$ as small as 14 nm and a significant shift in the temperature dependence of $\chi$. 20 Sub-10 nm domains have been achieved using this approach with poly(cyclohexylethylene)-b-PMMA 55 and recently feature sizes as small as 3 nm have been fabricated. 56 There is also some evidence that higher $\chi$ will lead to a reduction in the line edge roughness (LER). 51 LER values above a tolerable threshold will lead to a deterioration in the electrical properties of the integrated circuit. The degree to which the interface width correlates directly to changes in LER is still unknown.

Silicon-containing BCPs can achieve small pitches and have the advantage of inherently high etch contrast. Block copolymers with poly(dimethylsiloxane) are capable of achieving small feature sizes and good etch transfer to the underlying substrate. 14,17,56,57 In addition to polymers with silicon in the backbone, a series of BCPs with silicon-containing pendant groups have recently been synthesized and studied for DSA applications. 15,58–60 These include (in order of increasing $\chi$) PS-b-poly(trimethylsilylstyrene) (PS-b-PTMSS), PS-b-poly(pentamethyldisilystyrene) (PS-b-PDSS), poly(4-methoxy-styrene)-b-PTMSS (PMOST-b-PTMSS), PMOST-b-PDSS, and poly(5-vinyl-1,3-benzodioxole)-b-PDSS (PVBD-b-PDSS). DSA of PVBD-b-PDSS was recently demonstrated with half-pitches of 5 nm on a hybrid chemo/graphoepitaxial template. In this study we examine the interface width and $L_0$ scaling for a series of BCPs with $\chi$ ranging from $\approx$0.04 (a similar magnitude to that of PS-b-PMMA) to $\approx$0.25 (as determined by SAXS measurements on materials in the disordered phase). The interface widths are characterized using RSoXR to enhance the scattering contrast between the two blocks. Limits on the ratio of $w_M/L_0$ are explored as a function of $\chi N$ which helps explain experimental results demonstrating lower pitch limits on BCP etch transfer.

**MATERIALS AND METHODS**

**Sample Preparation.** Block copolymers were prepared via anionic polymerization using the techniques described by Durand et al. 15 Block copolymer solutions (3–5 wt % in methyl isobutyl ketone) were spin coated between 1500 and 3000 rpm to create smooth films on a silicon wafer with native oxide. In this study, it is generally observed that the silicon-containing block prefers to wet the air interface while the other block prefers to wet the substrate surface. The film thicknesses were $(n + 0.5)L_0$ where $n$ is an integer. Films were annealed at 180 °C for 10 min and inspected by optical microscopy to confirm that no topography formed during the annealing process.
RSoXR. RSoXR measurements were performed at the Advanced Light Source (ALS) at the Lawrence Berkeley National Laboratory using beamline 6.3.2. Measurements at the carbon edge (260−300 eV) were conducted using a 600 mm−1 grating, a 600 nm Ti filter, and a Burle CEM detector. Measurements at the oxygen edge (520−540 eV) were conducted using a 1200 mm−1 grating, a Cr filter, and the Burle CEM detector. The data were fit using the Refl1D program and uncertainties determined using the differential evolution adaptive metropolis (DREAM) algorithm.

RESULTS AND DISCUSSION

The properties of the BCPs examined in this study are outlined in Table 1. For all samples the interaction parameter was previously determined using SAXS measurements in the disordered state.

Table 1. Sample Parameters, χe, wM, and L0 from RSoXR Measurements

<table>
<thead>
<tr>
<th>sample name</th>
<th>Mn [kg/mol] (A block)</th>
<th>Mn [kg/mol] (B block)</th>
<th>N°</th>
<th>χe(SAXS)° at 180 °C</th>
<th>χe N (SAXS)</th>
<th>wM (Å)</th>
<th>L0 (Å)</th>
</tr>
</thead>
<tbody>
<tr>
<td>PS-b-PTMSS392</td>
<td>14.0</td>
<td>14.4</td>
<td>392</td>
<td>0.047</td>
<td>19.1</td>
<td>63.9</td>
<td>[−3.9/+9.8]</td>
</tr>
<tr>
<td>PS-b-PTMSS478</td>
<td>16.7</td>
<td>17.4</td>
<td>478</td>
<td>0.047</td>
<td>23.3</td>
<td>53.6</td>
<td>[1.3/+5.3]</td>
</tr>
<tr>
<td>PS-b-PTMSS656</td>
<td>23.7</td>
<td>23.2</td>
<td>656</td>
<td>0.047</td>
<td>32.0</td>
<td>44.6</td>
<td>[−1.0/+6.9]</td>
</tr>
<tr>
<td>PS-b-PDSS125</td>
<td>15.0</td>
<td>14.7</td>
<td>426</td>
<td>0.112</td>
<td>52.3</td>
<td>34.2</td>
<td>[−1.4/+3.8]</td>
</tr>
<tr>
<td>PMOST-b-PTMSS140</td>
<td>14.4</td>
<td>13.0</td>
<td>369</td>
<td>0.135</td>
<td>58.7</td>
<td>29.8</td>
<td>[−0.8/+1.3]</td>
</tr>
<tr>
<td>PMOST-b-PDSS125</td>
<td>7.4</td>
<td>5.9</td>
<td>182</td>
<td>0.195</td>
<td>38.5</td>
<td>22.0</td>
<td>[−1.3/+2.0]</td>
</tr>
<tr>
<td>PMOST-b-PDSS251</td>
<td>9.7</td>
<td>8.5</td>
<td>251</td>
<td>0.195</td>
<td>53.0</td>
<td>22.4</td>
<td>[−1.2/+1.8]</td>
</tr>
<tr>
<td>PVBD-b-PDSS182</td>
<td>12.3</td>
<td>12.5</td>
<td>345</td>
<td>0.195</td>
<td>72.7</td>
<td>22.8</td>
<td>[−1.3/+1.8]</td>
</tr>
<tr>
<td>PVBD-b-PDSS218</td>
<td>8.9</td>
<td>7.4</td>
<td>218</td>
<td>0.25</td>
<td>65.3</td>
<td>19.0</td>
<td>[−1.1/+1.9]</td>
</tr>
</tbody>
</table>

aN was calculated using eq 1, densities were experimentally determined previously, and a common reference volume of v0 = 118 Å3 was used for all samples. All values were calculated at 180 °C, based on SAXS measurements of disordered materials.

RSoXR measurements were performed at the Advanced Light Source (ALS) at the Lawrence Berkeley National Laboratory using beamline 6.3.2. Measurements at the carbon edge (260−300 eV) were conducted using a 600 mm−1 grating, a 600 nm Ti filter, and a Burle CEM detector. Measurements at the oxygen edge (520−540 eV) were conducted using a 1200 mm−1 grating, a Cr filter, and the Burle CEM detector. The data were fit using the Refl1D program and uncertainties determined using the differential evolution adaptive metropolis (DREAM) algorithm.

RESULTS AND DISCUSSION

The properties of the BCPs examined in this study are outlined in Table 1. For all samples the interaction parameter was previously determined using SAXS measurements in the disordered state.

The results of the RSoXR measurements on the PMOST-b-PDSS series are shown in Figure 1, where χe N ranged from 32 to 60. The reflectivity curves (Figure 1A) show the classic multilayer signature of a BCP oriented parallel to the substrate. The higher frequency fringes correspond to the total thickness of the film, and the longer spacing between the Bragg peaks corresponds to the L0 of the polymer. The film prepared from the lowest molecular weight sample (PMOST-b-PDSS182) has the greatest number of repeating layers in the film (9 full multilayers) and as a result had the sharpest Bragg peaks. The Bragg peak intensity is a function of both the contrast between
the layers and the total number of repeating layers. Both the second-order \((q \cong 0.14 \text{ Å}^{-1})\) and third-order \((q \cong 0.24 \text{ Å}^{-1})\) Bragg peaks are clearly visible, showing the slow decay of the Bragg peak intensity. The best fit to this sample results in a \(w_M = 22.0 \pm 1.2\) Å. The samples with larger molecular weights (PMOST-b-PDSS156, PMOST-b-PDSS182) show similar behaviors, including both the high frequency fringes and the lower frequency Bragg peaks. As the molecular weight increases, the spacing between the Bragg peaks decreases, consistent with the increase in the BCP domain pitch. The magnitude of the Bragg peaks also decreases because of the reduced number of multilayers in the film. All three samples at different \(M_w\) show effectively the same \(w_M\) at 22.4 [\(-1.3/1.8\)] Å and 22.8 [\(-1.3/1.8\)] Å for PMOST-b-PDSS156 and PMOST-b-PDSS182, respectively. All samples show asymmetry in the uncertainties for \(w_M\) with the uncertainty in the positive direction being larger than the uncertainty in the negative direction. Shrinking the interface width has a larger impact on the simulated reflectivity than increasing it, and this results in the asymmetry of the uncertainty.

In addition to the results shown in Figure 1, RSoXR measurements were conducted on the remainder of the samples outlined in Table 1. The pitch scaling was explored in order to place the results in context with the behavior of previously investigated BCPs with similar \(\chi N\). The results of those measurements are shown in the Supporting Information. Figure 2 shows a \(\ln \ln (L_0)\) as a function of \(N\) for the three series where multiple molecular masses were examined. All three series show \(L_0 \sim N^{3/4}\), a stronger scaling than predicted in either the WSL (\(N^{1/2}\)) or SSL (\(N^{2/3}\)). The scaling observed here is closer to previous results which sometimes observed an \(N^{5/3}\) scaling in samples with similar \(\chi N\) (35–80), a regime which is associated with stretched Gaussian coils. The origin of the scaling behavior in this region is unclear, but it is shown here to be consistent among samples with a range of \(\chi N\).

For high molecular weight BCPs the interface width is generally small relative to the pitch; for systems near the ODT, the interface region can constitute a significant portion of the BCP. Figure 3 shows the ratio of \(w_M/L_0\) as a function of \(\chi N\). The PS-b-PTMSS series ranges between \(\chi N = 15\) and 35, and in this region \(w_M/L_0\) can be seen to increase rapidly with decreasing \(\chi N\), particularly as the ODT is approached (using eq 2 the \((\chi N)_{ODT} \approx 13–15\) for most systems investigated in this study). For \(\chi N > 30\) the \(w_M/L_0\) gradually reduces with increasing \(\chi N\); this effect is well captured by the PMOST-b-PDSS series which spans 40 < \(\chi N < 70\). The two materials with the largest \(\chi N\) investigated show \(w_M/L_0\) of just above 0.10.

Figure 3. Ratio of \(w_M/L_0\) as a function of \(\chi N\). From these results a scaling relationship can be extracted, \(w_M/L_0 \sim (\chi N)^{\alpha}\). For \(\chi N < 35\ \omega \approx -3/2\), and for \(\chi N > 35\ \omega \approx -2/3\). For systems with \(w_M/L_0\) above 0.27 (dashed line) experimental results have shown a loss of alignment upon etching one of the components in the polymer. There is some spread in the data in this region, which may be caused in part by conformational asymmetry between the two components of the block copolymer which is not captured in this straightforward scaling approach. Separating the results into regions above and below \(\chi N = 35\) allows two different scaling relationships to be extracted from \(w_M/L_0 \sim (\chi N)^{\alpha}\). In the region below \(\chi N = 35\), \(\omega \approx -3/2\); above \(\chi N = 35\), \(\omega \approx -2/3\). Attempting to fit this data with a single power law exponent generally resulted in poor fits to the data below \(\chi N = 35\); given that the pitch scaling is well-known, this suggests a shift in the scaling of the interface width as the ODT is approached. Experimental results have shown that when \(w_M/L_0\) \(\geq 0.27\), etch transfer of a DSA patterned BCP results in large numbers of defects; this limit in relation to the samples investigated in this study is marked in Figure 3. The origin of this behavior can be explained by examining the composition profiles as a function of \(\chi N\).

The impact of the interface width on the composition profile is captured in Figure 4, which shows the composition profiles for BCP samples with \(\chi N\) ranging from 19.1 to 72.7. The profiles are normalized by the BCP \(L_0\) to compare materials with a wide range of \(L_0\) on the same graph. PS-b-PTMSS182 has the lowest \(\chi N\) value (19.1) and shows both a sinusoidal composition profile and evidence of incomplete phase segregation (i.e., significant regions with composition very close to 1.0 or 0.0 are not observed). PS-b-PTMSS182 has a slightly larger \(\chi N\) (23.3) and now shows a narrow region of complete phase segregation near the center of the lamella. As \(\chi N\) increases, the composition profile rapidly shows signs of increasing phase separation. Increasing \(\chi N\) to 38.3 (PMOST-b-PDSS182) shows a clear transition to the square wave profile associated with the SSL, although the interface still makes up a considerable portion of the profile. PMOST-b-PDSS182 has the largest \(\chi N\) examined in this study and results in lamella with a narrow interface. The incomplete phase segregation at \(\chi N = 19.1\) demonstrates why this represents a lower limit on the patterning ability of BCPs. While the overall structure still results in a lamellar morphology local composition fluctuations are significant enough to result in incomplete phase segregation at many positions along the lamellae. Upon etch transfer these composition fluctuations result in defects. This could be even more problematic near the neutral brush, which likely acts as a compatibilizer and shifts the local \((\chi N)_{ODT}\) to a higher value.

Both TEM and scattering measurements have suggested that
the magnitude of fluctuations increases near the neutral brush. It is also possible that this effective patterning limit will shift for BCPs with lower $N$, where composition fluctuation effects may have a greater impact.

The lower accessible limit of $w_m/L_0$ for a given $L_0$ will depend on $\chi_e$ and therefore vary depending on the BCP system. This is explored in Figure 5 where $w_m/L_0$ is shown as a function of $L_0$. PS-b-PTMSS has the lowest $\chi_e$ of the BCPs investigated in this study, at $\chi_e \approx 0.04$. As a result, when $L_0$ decreases, $w_m/L_0$ increases rapidly, reaching 0.35 at $L_0 = 179$ Å, demonstrating that this system likely has a similar lower accessible pitch limit as PS-b-PMMA, which is consistent with the similar magnitude of $\chi_e$ for the two materials. As discussed in the previous paragraph, this sample shows incomplete phase segregation. This sample series demonstrates that for a material with this $\chi_e$ there is a clear barrier to achieving smaller $L_0 < 100$ Å while maintaining a sufficiently small interface width. As $\chi_e$ increases, this limit shifts to progressively lower values. PS-b-PDSS has a $\chi_e \approx 0.11$, and $w_m/L_0$ was found to be 0.17 at $L_0 = 195$ Å, a 40% reduction over the expected value for a PS-b-PTMSS sample with identical pitch ($w_m/L_0$ for PS-b-PTMSS with this pitch as extrapolated from the trend). This trend is continued as the BCPs with higher $\chi_e$ are examined, shifting the lower limits of $w_m/L_0$. A rough extrapolation of the data for PMOST-b-PDSS suggests that this system could reach a lower patterning limit of $L_0 \approx 90$ Å. While there is insufficient data to determine the lower limit of the PVBD-b-PDSS series, experimental results have demonstrated patterning and etch transfer down to $L_0 \approx 100$ Å, suggesting that the lower limits lie at even smaller $L_0$.

Extrapolating from these results also provides an estimate for the magnitude of $\chi_e$ which will be needed to obtain $w_m/L_0 < 0.1$ and $L_0 < 100$ Å, which is $\chi_e \approx 0.6$–0.7. This is on the order of the value reported for a recently synthesized polymer, polydihydroxystyrene-b-PS, providing additional hope that new BCPs can provide solutions to the patterning needs of next-generation technology nodes.  

### CONCLUSIONS

Block copolymer lithography requires materials with sufficiently low $w_m/L_0$ so that the composition fluctuations do not result in defects during etch transfer and the resulting LER does not inhibit electrical performance. By use of RSoXR, the composition profile of a series of high $\chi_e$ BCPs was characterized and $w_m/L_0$ was extracted. This value was scaled as a function of $\chi_e N$, demonstrating a rapid increase as the ODT is approached, and below $\chi_e N = 20$ incomplete phase segregation in the composition profile is observed. This coincides with experimental results showing difficulty in obtaining good etch transfer for a system with similar $w_m/L_0$, which provides strong evidence that composition fluctuations limited the etch transfer and that $w_m/L_0 \approx 0.27$ represents an upper limit for effective BCP lithography. $w_m/L_0$ was also scaled as a function of $L_0$, demonstrating a shift in the lower accessible $L_0$ under this limit with increasing $\chi_e$.

### ASSOCIATED CONTENT

#### Supporting Information

The Supporting Information is available free of charge on the ACS Publications website at DOI: 10.1021/acs.macromol.7b01982.

Figures S1–S4 (PDF)

### AUTHOR INFORMATION

**Corresponding Author**
*E-mail daniel.sunday@nist.gov (D.F.S.).*

**ORCID**
Daniel F. Sunday: 0000-0002-6840-535X  
Michael J. Maher: 0000-0003-0577-3726  
Adam F. Hannon: 0000-0002-7015-6858  
Gregory Blachut: 0000-0002-8539-4840  
Christopher J. Ellison: 0000-0002-0393-2941

DOI: 10.1021/acs.macromol.7b01982  
Macromolecules

C. Grant Willson: 0000-0002-2072-3981

Notes
The authors declare no competing financial interest.

ACKNOWLEDGMENTS

The Advanced Light Source is supported by the Director, Office of Science, Office of Basic Energy Sciences, of the U.S. Department of Energy under Contract DE-AC02-05CH11231. We thank Eric Gullikson for assistance at BL 6.3.2. and Paul Kienzle for the work developing the ReflID software. The authors thank Nissan Chemical Industries, Lam Research, the ASTC, and the National Science Foundation (Grants ECS-1120823 and EEC-1160494) for financial support. M.J.M. thanks National Science Foundation Graduate Research Fellowship (Grant DGE-1110007) for financial support. C.J.E. thanks the Welch Foundation (Grant #F-1709) for partial financial support. G.W. thanks the Rashid Engineering Regents Chair and the Welch Foundation (Grant #F-1830) for partial financial support. Any opinion, findings, and conclusions or recommendations expressed in this material are those of the authors and do not necessarily reflect the views of the National Science Foundation or the sponsors.

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